

ABSTRACT

REDUCED ASPECT RATIO DIGIT LINE CONTACT PROCESS FLOW USED DURING THE FORMATION OF A SEMICONDUCTOR DEVICE

A method used during the formation of a semiconductor device comprises forming a first portion of a digit line contact plug before forming storage capacitors. Subsequent to forming storage capacitors, a second portion of the digit line plug is formed to contact the first portion, then the digit line runner is formed to contact the second plug portion. A structure resulting from the process is also described.